Small Signal MOSFET

-20 V, -200 mA, Dual P-Channel, 1.0 x 1.0 mm SOT-963 Package

Features

- Dual P-Channel MOSFET
- Offers a Low R_{DS(on)} Solution in the Ultra Small 1.0 x 1.0 mm Package
- 1.5 V Gate Voltage Rating
- Ultra Thin Profile (< 0.5 mm) Allows It to Fit Easily into Extremely Thin Environments such as Portable Electronics.
- This is a Pb–Free Device

Applications

- High Side Switch
- High Speed Interfacing
- Optimized for Power Management in Ultra Portable Equipment

Para	Parameter			Value	Unit		
Drain-to-Source Voltag	V _{DSS}	-20	V				
Gate-to-Source Voltag	V _{GS}	±8	V				
Continuous Drain	Steady	$T_A = 25^{\circ}C$		-200			
Current (Note 1)	State	$T_A = 85^{\circ}C$	I _D	-140	mA		
	t ≤ 5 s	$T_A = 25^{\circ}C$		-250			
Power Dissipation	Steady			-125			
(Note 1)	State	$T_A = 25^{\circ}C$	PD		mW		
	t ≤ 5 s			-200			
Pulsed Drain Current	$Current t_p = 10 \ \mu s I_{DM} -600 mA$			mA			
Operating Junction and	Storage Terr	perature	TJ,	-55 to	°C		
	T _{STG}	150					
Source Current (Body Diode) (Note 2)			IS	-200	mA		
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)					°C		

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability. 1. Surface-mounted on FR4 board using the minimum recommended pad size,

1 oz Cu.

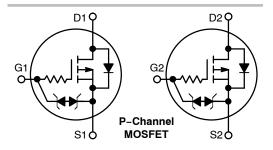
2. Pulse Test: pulse width \leq 300 μ s, duty cycle \leq 2%

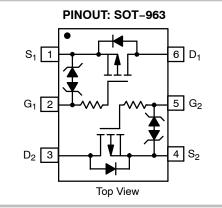


ON Semiconductor®

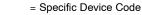
http://onsemi.com

V _{(BR)DSS}	R _{DS(ON)} MAX	I _D Max	
–20 V	5.0 Ω @ –4.5 V		
	6.0 Ω @ –2.5 V	-0.2 A	
	7.0 Ω @ –1.8 V	-0.2 A	
	10 Ω @ –1.5 V		









= Date Code

4

Μ

.

= Pb-Free Package

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

MAXIMUM RATINGS (T = 25°C unless otherwise specified)

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Мах	Unit
Junction-to-Ambient - Steady State (Note 3)	$R_{\theta JA}$	1000	°C/W
Junction-to-Ambient - t = 5 s (Note 3)		600	

3. Surface-mounted on FR4 board using the minimum recommended pad size, 1 oz Cu.

ELECTRICAL CHARACTERISTICS ($T_J = 25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test Condition		Min	Тур	Max	Unit
OFF CHARACTERISTICS	-	-		-	-	· · ·	
Drain-to-Source Breakdown Voltage	V _{(BR)DSS}	$V_{GS} = 0 V, I_D = -250 \mu A$		-20			V
Zero Gate Voltage Drain Current	I _{DSS}	V_{GS} = 0 V, V_{DS} = -5.0 V	$V_{GS} = 0 V, V_{DS} = -5.0 V$ $T_{J} = 25^{\circ}C$			-50	
		V_{GS} = 0 V, V_{DS} = -5.0 V	$T_J = 85^{\circ}C$			-100	nA
		$V_{GS} = 0 V, V_{DS} = -16 V$	$T_J = 25^{\circ}C$			-200	
Gate-to-Source Leakage Current	I _{GSS}	V_{DS} = 0 V, V_{GS} = ±5.0 V				±100	nA
ON CHARACTERISTICS (Note 4)	•	•					
Gate Threshold Voltage	V _{GS(TH)}	$V_{GS} = V_{DS}$, $I_D = -250 \ \mu A$		-0.4		-1.0	V
Drain-to-Source On Resistance	R _{DS(ON)}	$V_{GS} = -4.5 \text{ V}, \text{ I}_{D} = -100 \text{ mA}$			2.0	5.0	Ω
		$V_{GS} = -2.5 \text{ V}, \text{ I}_{D} = -50 \text{ mA}$			2.6	6.0	
		$V_{GS} = -1.8$ V, $I_D = -20$ mA			3.4	7.0	
		$V_{GS} = -1.5$ V, $I_D = -10$ mA			4.0	10	
		$V_{GS} = -1.2 \text{ V}, \text{ I}_D = -1.0 \text{ mA}$			6.0		
Forward Transconductance	9FS	$V_{DS} = -5.0 \text{ V}, \text{ I}_{D} = -125 \text{ mA}$			0.35		S
Source-Drain Diode Voltage	V _{SD}	$V_{GS} = 0 \text{ V}, \text{ I}_{S} = -10 \text{ mA}$			-0.6	-1.0	V
CHARGES, CAPACITANCES AND GATE	RESISTANCE				-		
Input Capacitance	C _{ISS}				13.5		
Output Capacitance	C _{OSS}	$ f = 1 \text{ MHz}, V_{GS} = 0 \text{ V} $ $ V_{DS} = -15 \text{ V} $			3.8		pF
Reverse Transfer Capacitance	C _{RSS}				2.0		
SWITCHING CHARACTERISTICS, V_{GS} =	4.5 V (Note 4)	-		-	-	-	
Turn-On Delay Time	t _{d(ON)}	V_{GS} = -4.5 V, V_{DD} = -15 V, I_D = -200 mA, R_G = 2.0 Ω			26		- ns
Rise Time	t _r				46		
Turn-Off Delay Time	t _{d(OFF)}				196		
Fall Time	t _f				145		

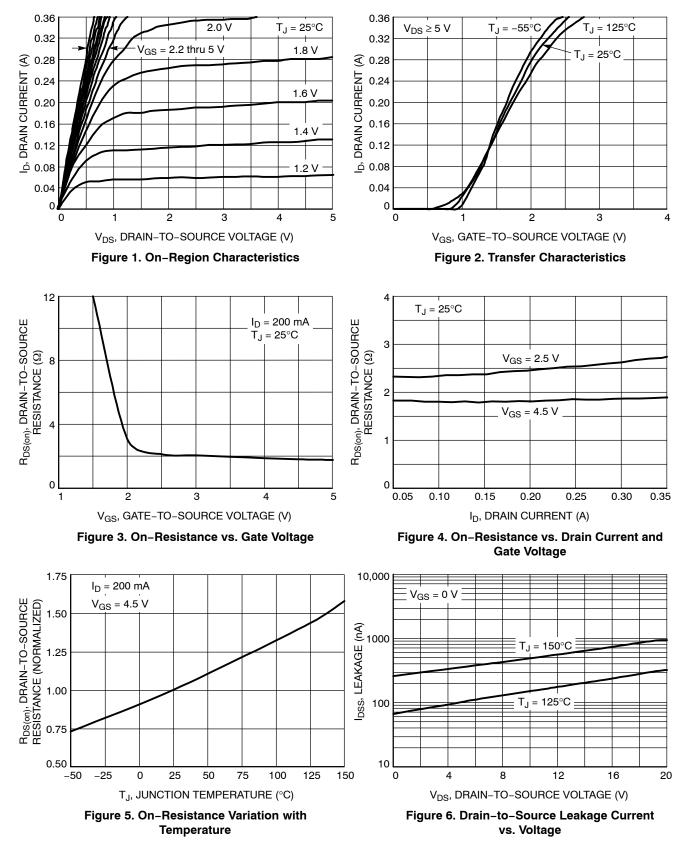
4. Switching characteristics are independent of operating junction temperatures

ORDERING INFORMATION

Device	Package	Shipping [†]		
NTUD3171PZT5G	SOT-963 (Pb-Free)	8000 / Tape & Reel		

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.





TYPICAL CHARACTERISTICS

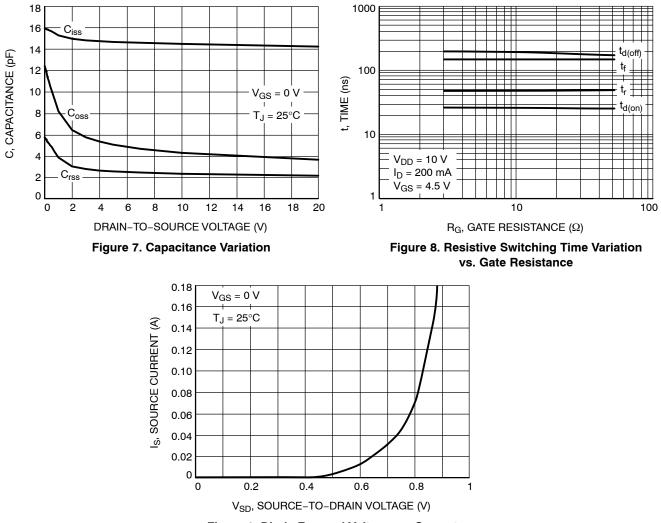
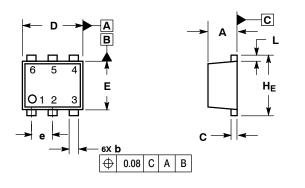


Figure 9. Diode Forward Voltage vs. Current

PACKAGE DIMENSIONS

SOT-963 CASE 527AD-01 ISSUE D

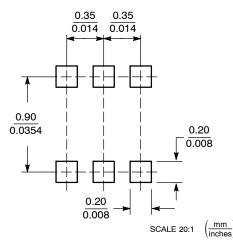


NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- TI4-300, 1962. CONTROLLING DIMENSION: MILLIMETERS MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS, MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL. 3.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.34	0.37	0.40			
b	0.10	0.15	0.20	0.004	0.006	0.008
С	0.07	0.12	0.17	0.003	0.005	0.007
D	0.95	1.00	1.05	0.037	0.039	0.041
ш	0.75	0.80	0.85	0.03	0.032	0.034
e	0.35 BSC			0.014 BSC		
L	0.05	0.10	0.15	0.002	0.004	0.006
ΗE	0.95	1.00	1.05	0.037	0.039	0.041
HE						

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

ON Semiconductor and 💷 are registered trademarks of Semiconductor Components Industries, LLC (SCILLC). SCILLC reserves the right to make changes without further notice ON Semiconductor and up are registered trademarks of Semiconductor Components Industries, LLC (SCILLC). SCILLC reserves the right to make changes without further notice to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights on or the rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use pervised use as complex trendend reparation to the design or unauthorized use pervises. associated with such unintended or unauthorized use, even if such claim alleges that SCILLC was negligent regarding the design or manufacture of the part. SCILLC is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor P.O. Box 5163, Denver, Colorado 80217 USA Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada Email: orderlit@onsemi.com

N. American Technical Support: 800-282-9855 Toll Free USA/Canada Europe, Middle East and Africa Technical Support:

Phone: 421 33 790 2910 Japan Customer Focus Center Phone: 81-3-5773-3850

ON Semiconductor Website: www.onsemi.com

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative